

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1	((substrate wafer) near (cutting near different)) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:28
L3	27	((substrate wafer) near (cutting)) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:30
L15	2036	438/507,566-569,74,77,81,93-94. ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:33
L19	5	((cutting near (plane\$1 position\$1))) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:35
L20	5	(((cutting dicing segment\$3dividing) near (plane\$1 position\$1))) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L21	0	20 not 19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L22	5355	(((plane\$1 position\$1))) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L23	4709	257/443,448,459,461,466.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36

L24	6633	15 or 23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L25	4709	23 and 24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:36
L26	41	22 and 24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:37
L27	1	("2002/0168856").URPN.	USPAT	OR	ON	2010/09/17 10:38
L28	101	((cutting)) same (depend depending) same (resistivity resistivities) same temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:40
L29	135715	vapor near phase	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:40
L30	2	28 and 29	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 10:40
L32	19	("3651386" "4454495" "4919542" "4996077" "5154514" "5245309" "5297438" "5415699" "5429070" "5435646" "5493266" "5502355" "5564830" "5614055" "5831277" "5900071" "5907161" "5947601").PN. OR ("6257760"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/17 10:47
L33	12	("20010053600" "5326170" "5331676" "5593923" "5780360" "6132081" "6136613" "6136699" "6257760" "6329670" "6399487"). PN. OR ("6517235").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2010/09/17 10:48
L35	2	("2003/0077870").URPN.	USPAT	OR	ON	2010/09/17 11:41
L36	0	(Fe near InP) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	USPAT	OR	ON	2010/09/17 11:43

L37	0	(Fe near InP) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:43
L38	0	(Fe near semiconductor) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:43
L39	0	(single near crystal) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:44
L40	2	(substrate) with (cutting) with (temperature resistivity) with (heating) with (epitaxy epitaxially epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:44
L41	35622	(epitaxy epitaxially epitaxial) with (vapor phase near reproducible)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L42	0	(epitaxy epitaxially epitaxial) with (vapor near phase near reproducible)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L43	16626	(epitaxy epitaxially epitaxial) with (vapor near phase)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L44	3205	(single near crystal) with cutting	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:48
L45	85	((single near crystal) with cutting) with (heating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49

L46	0	43 and 45	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49
L47	6974	(substrate wafer) with (epitaxy epitaxially epitaxial) with (vapor near phase))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49
L48	104	44 and 47	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:49
L49	6752	(substrate wafer) with (epitaxy epitaxial) with (vapor near phase))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:52
L50	100	44 and 49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:52
L51	1	"10589733"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 11:55
L52	0	(vapor near phase near reproducible)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:02
L53	0	(vapor near phase near reproduc\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:02
L54	5093	(vapor near phase near produc\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:02

L55	0	(vapor near phase near (re near produc\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:03
L56	5829	(substrates) with (epitaxial epitaxy) with (vapor near phase)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:03
L57	96	44 and 56	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:03
L58	457	(Fe near InP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:04
L59	1	57 and 58	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/09/17 12:04

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